

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
40V	10mΩ @ V <sub>GS</sub> = 10V	80A

**Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- DC-DC converters
- Body control electronics

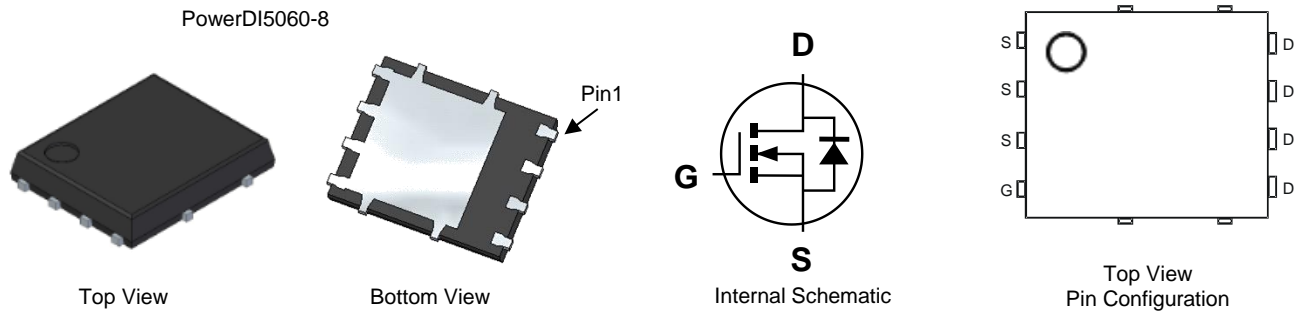
**Features and Benefits**

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Q<sub>g</sub> – Minimizes Switching Loss
- Low R<sub>DS(ON)</sub> – Minimizes On State Loss
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMNH4011SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

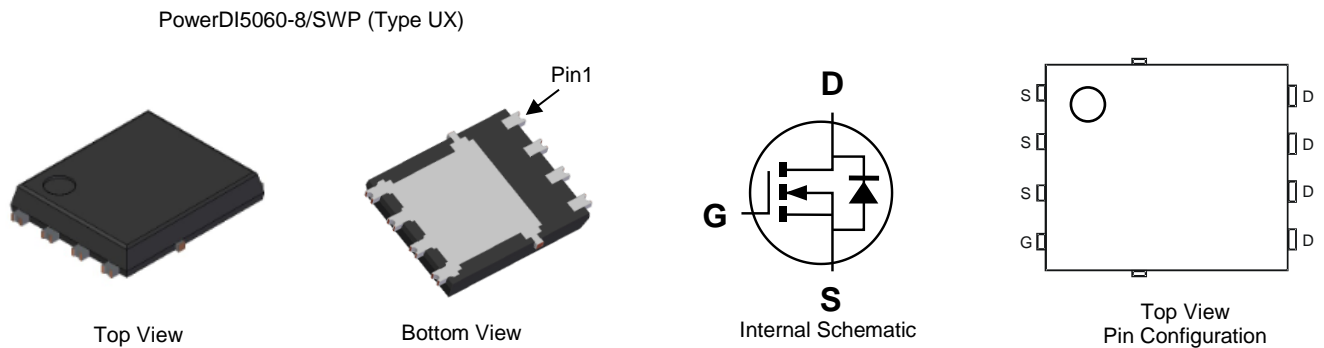
**Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe, Solderable per MIL-STD-202, Method 208 <sup>Ⓔ3</sup>
- Weight: 0.097 grams (Approximate)

**Site 1:**



**Site 2:**



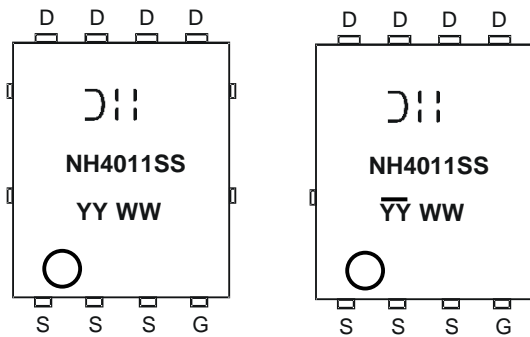
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.  
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.  
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

### Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty	Carrier
DMNH4011SPSQ-13	PowerDI5060-8	2,500	Reel
	PowerDI5060-8/SWP (Type UX)	2,500	Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

### Marking Information



D I I = Manufacturer's Marking  
 NH4011SS = Product Type Marking Code  
 YYWW or YYWW = Date Code Marking  
 YY or YY = Year (ex: 23 = 2023)  
 WW = Week (01 to 53)

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C	13	A
	T <sub>A</sub> = +70°C	10.8	A
	T <sub>C</sub> = +25°C	80	A
	T <sub>C</sub> = +100°C (Note 8)	57	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	90	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	80	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	90	A
Avalanche Current, L = 1mH	I <sub>AS</sub>	18	A
Avalanche Energy, L = 1mH	E <sub>AS</sub>	170	mJ

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.  
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 8. Short duration pulse test used to minimize self-heating effect.

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_D$	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	60	$^{\circ}C/W$
Total Power Dissipation (Note 7)	$P_D$	150	W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	1	$^{\circ}C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^{\circ}C$

## Electrical Characteristics (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 40V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8.5	10	m $\Omega$	$V_{GS} = 10V, I_D = 50A$
Diode Forward Voltage	$V_{SD}$	—	0.9	1.2	V	$V_{GS} = 0V, I_S = 50A$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	1405	—	pF	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$
Output Capacitance	$C_{oss}$	—	247	—		
Reverse Transfer Capacitance	$C_{rss}$	—	108	—		
Gate Resistance	$R_g$	—	2.2	—	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	$Q_g$	—	25.5	—	nC	$V_{DS} = 20V, V_{GS} = 10V, I_D = 50A$
Gate-Source Charge	$Q_{gs}$	—	4.6	—		
Gate-Drain Charge	$Q_{gd}$	—	6.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.6	—	ns	$V_{DD} = 20V, V_{GS} = 10V, I_D = 50A, R_G = 3.5\Omega$
Turn-On Rise Time	$t_r$	—	3.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	16	—		
Turn-Off Fall Time	$t_f$	—	5.1	—		
Body Diode Reverse Recovery Time	$t_{RR}$	—	22.1	—	ns	$I_f = 50A, di/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{RR}$	—	13.4	—	nC	

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.

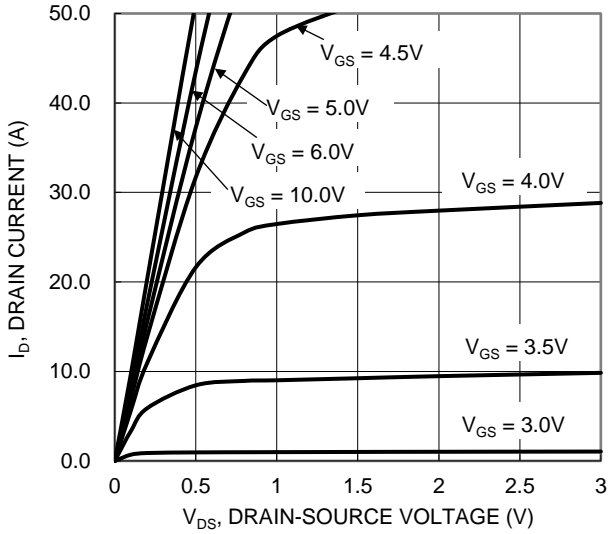


Figure 1 Typical Output Characteristic

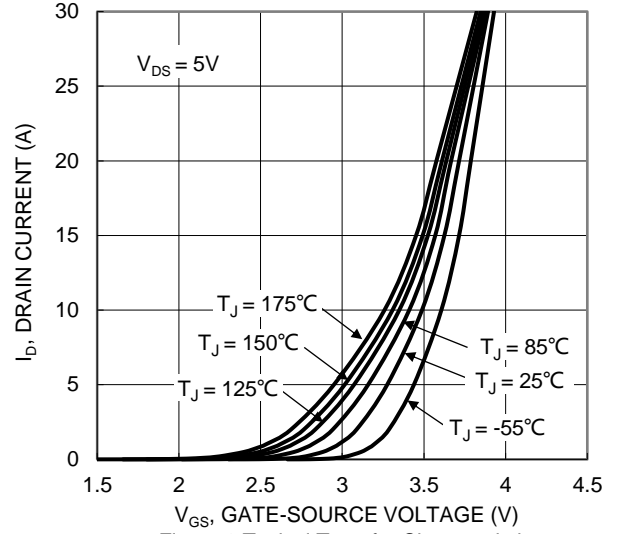


Figure 2 Typical Transfer Characteristic

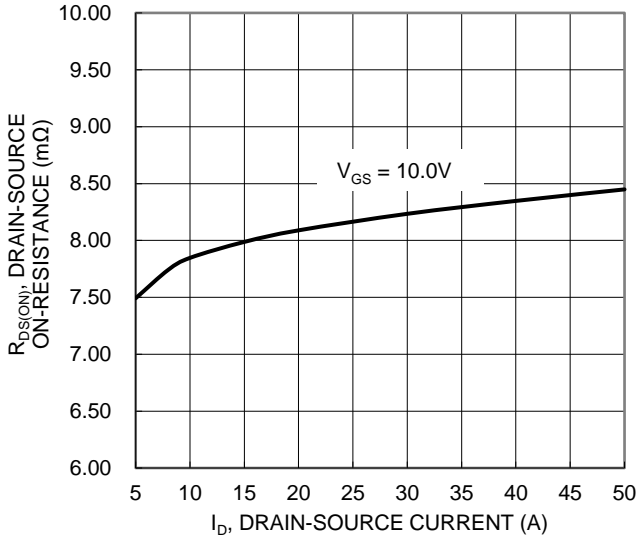


Figure 3 Typical On-Resistance vs Drain Current and Gate Voltage

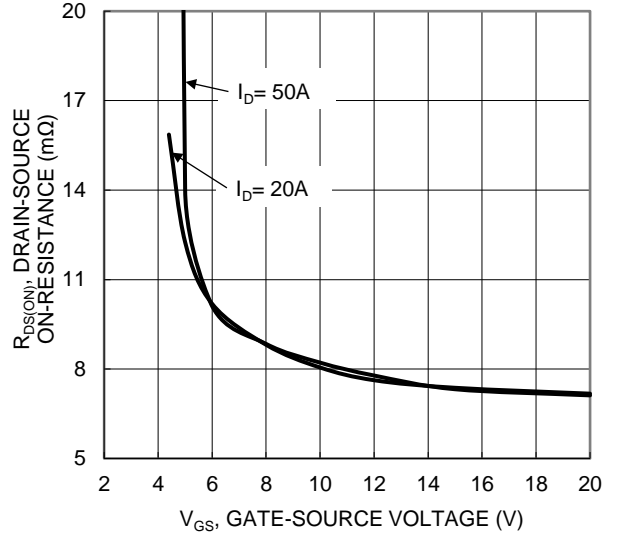


Figure 4 Typical Transfer Characteristic

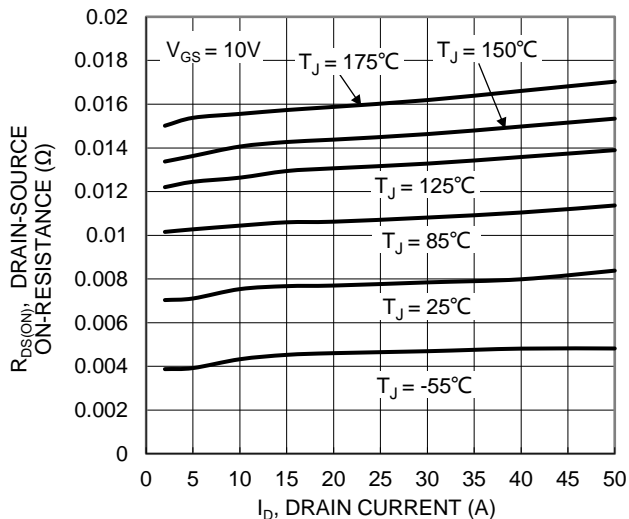


Figure 5 Typical On-Resistance vs Drain Current and Temperature

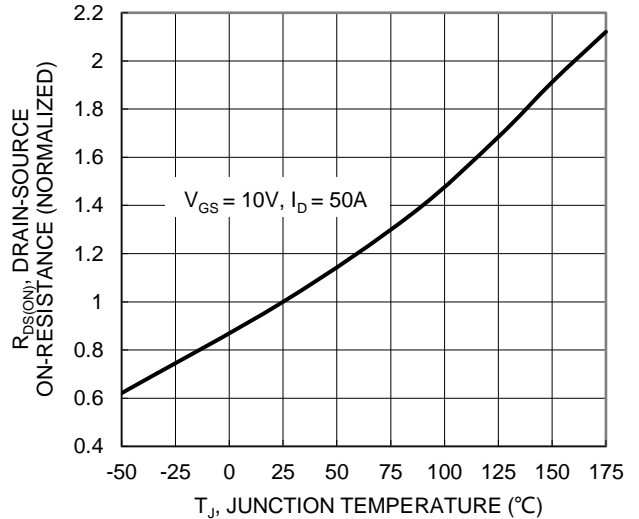


Figure 6 On-Resistance Variation with Temperature

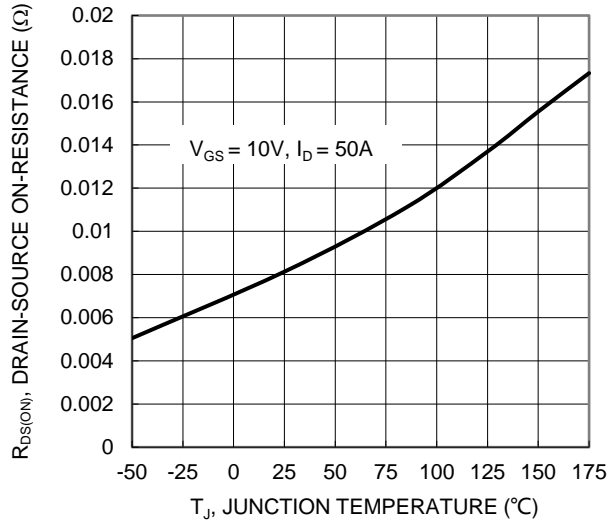


Figure 7 On-Resistance Variation with Temperature

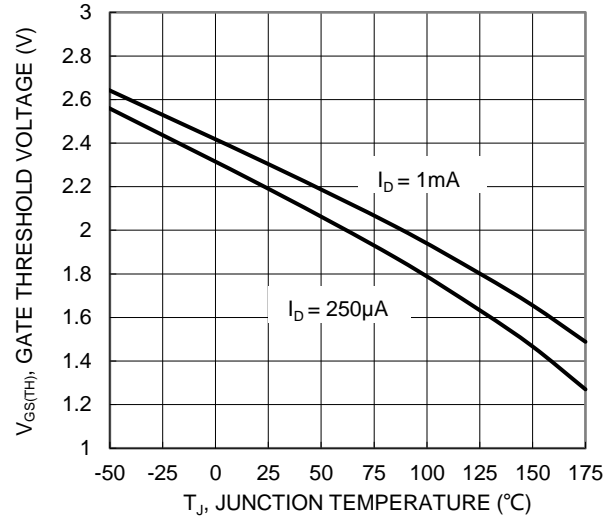


Figure 8 Gate Threshold Variation vs Temperature

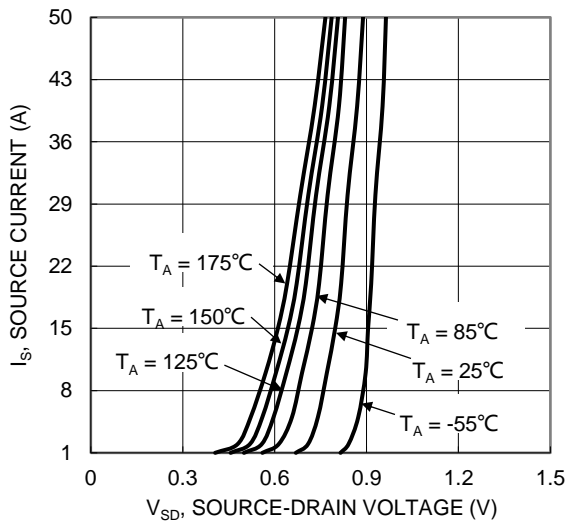


Figure 9 Diode Forward Voltage vs Current

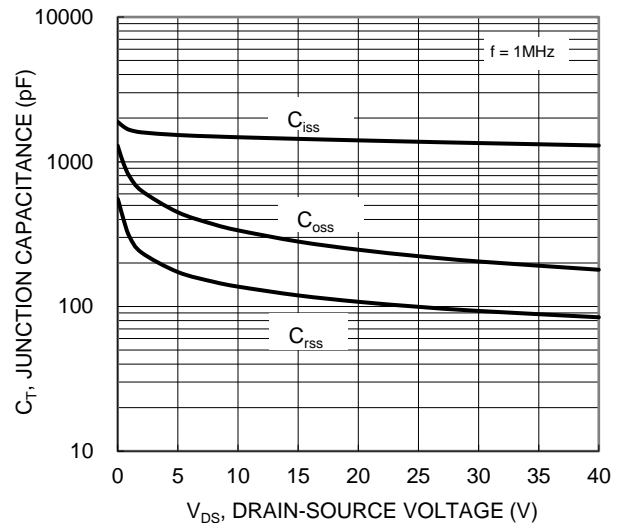


Figure 10 Typical Junction Capacitance

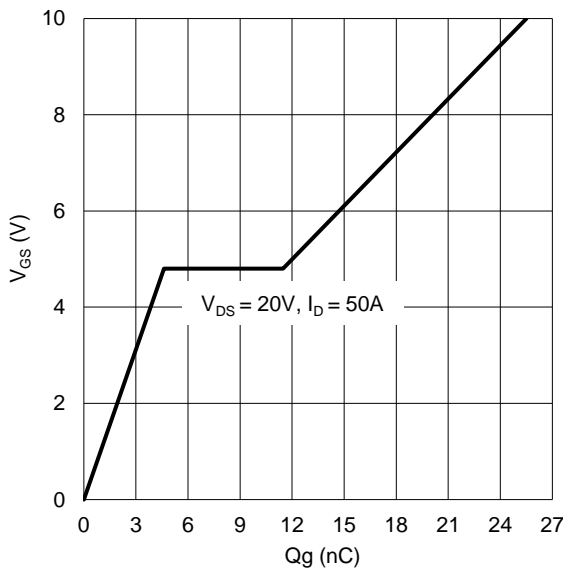


Figure 11 Gate Charge

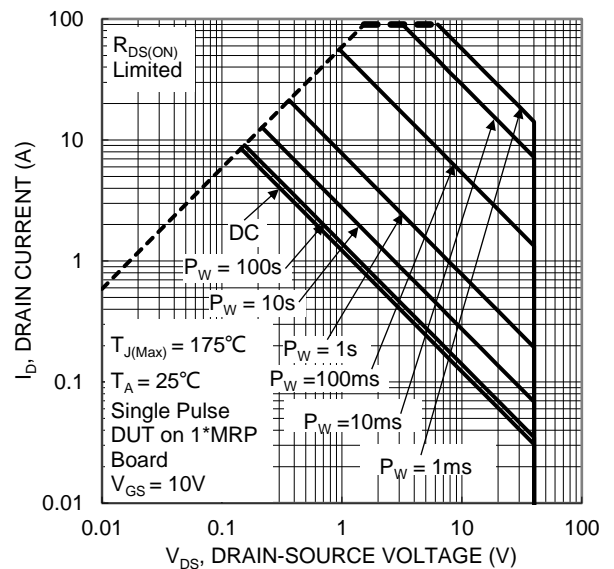


Figure 12 SOA, Safe Operation Area

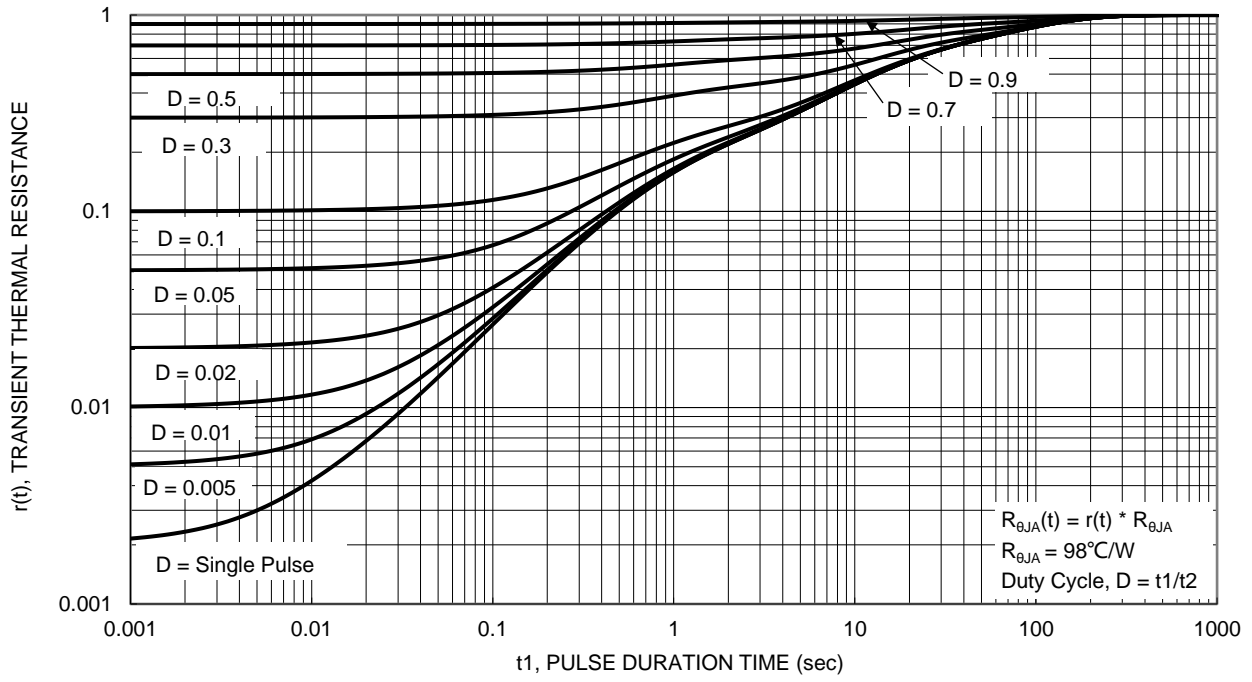


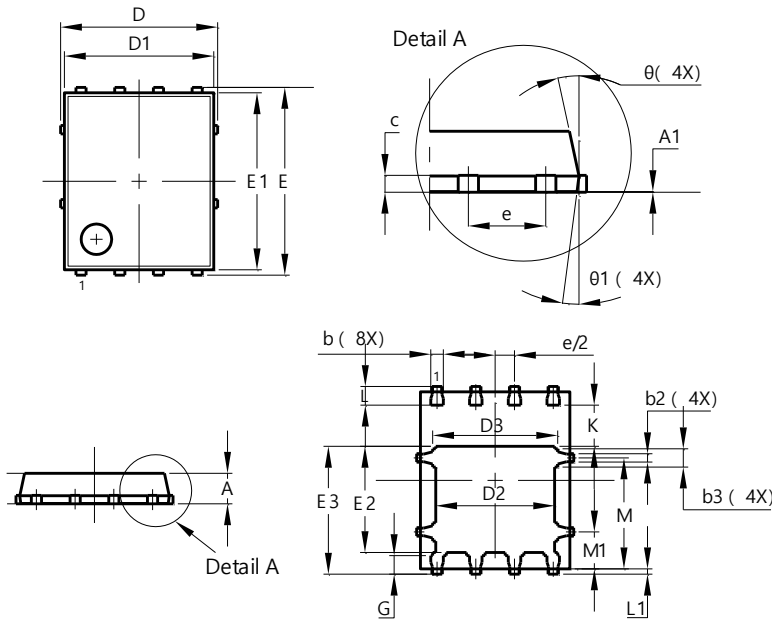
Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

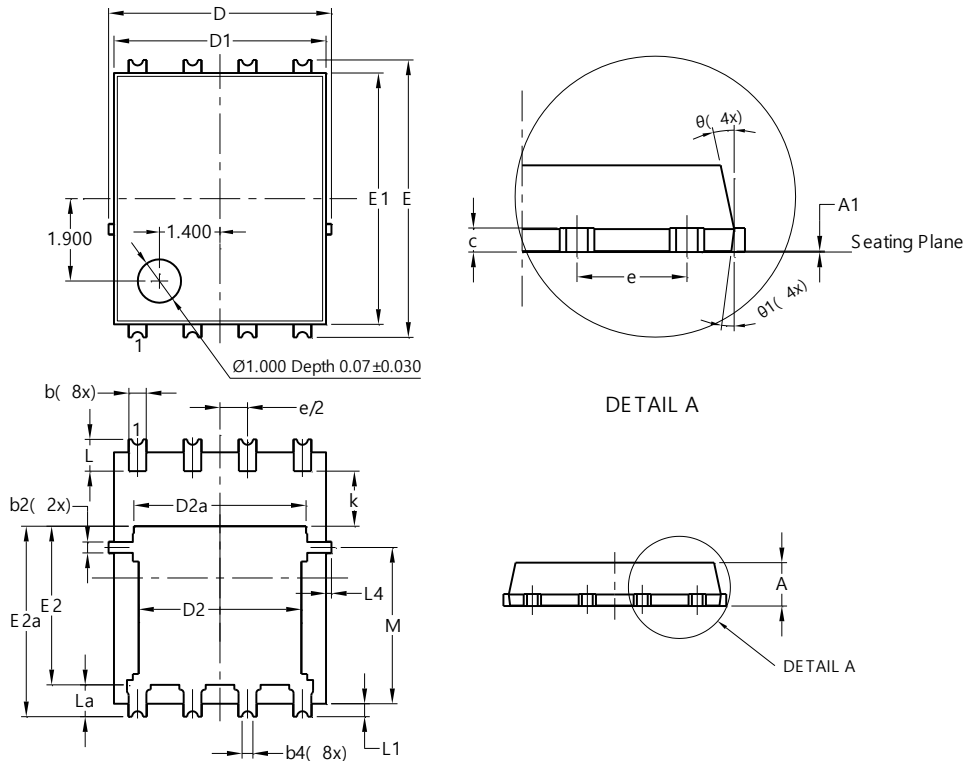
**PowerDI5060-8**



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Site 2:

**PowerDI5060-8/SWP (Type UX)**



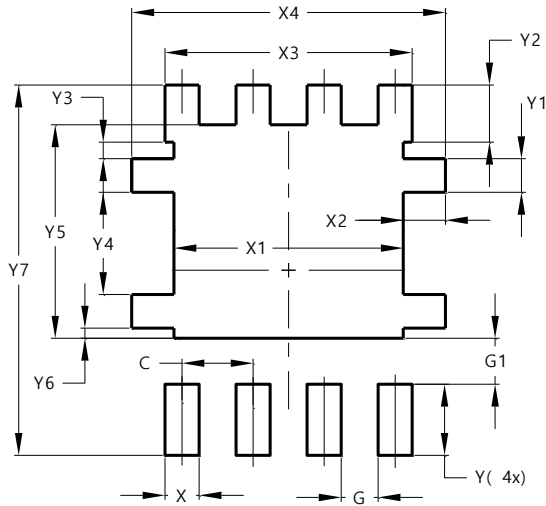
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

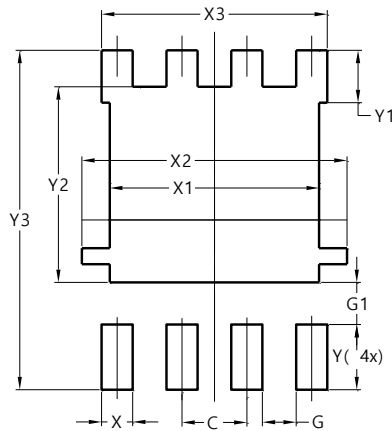
**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

**PowerDI5060-8/SWP (Type UX)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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